



Features

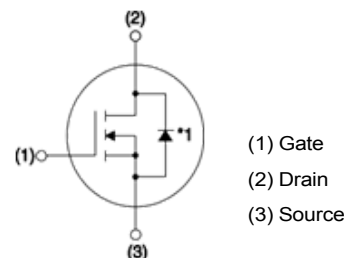
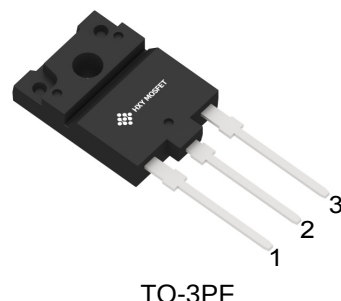
- Effectively lower down T_j and R_{th} , high anti-EMI ability
- High Blocking Voltage with Low $R_{DS(on)}$
- Easy to Parallel and Simple to Drive
- Ultra-low Drain-Gate capacitance
- Halogen Free, RoHS Compliant

Benefits

- Higher system efficiency
- Reduce cooling requirements
- Increase power density
- Increase system switching frequency

Applications

- Auxiliary Power Supplies Switch
- Mode Power Supplies
- High-Voltage Capacitive Loads



Ordering Part Number	Package	Brand
IMWH170R1K0M1XKSA1	TO-3PF	HXY MOSFET

Maximum Ratings ($T_c = 25^\circ\text{C}$ unless otherwise specified)

Symbol	Parameter	Value	Unit	Test Conditions	Note
V_{DSmax}	Drain-Source Voltage	1700	V	$V_{GS}=0V, I_D=100\mu A$	
V_{GSmax}	Gate-Source Voltage	-8/+22	V	Absolute maximum values	
V_{GSop}	Gate-Source Voltage	-4/+18	V	Recommended operational values	
I_D	Continuous Drain Current	5.0	A	$V_{GS}=20V, T_c=25^\circ\text{C}$	Fig. 19
		3.5		$V_{GS}=20V, T_c=100^\circ\text{C}$	
$I_{D(pulse)}$	Pulsed Drain Current	15	A	Pulse width t_p limited by T_{Jmax}	Fig. 22
P_D	Power Dissipation	69	W	$T_c=25^\circ\text{C}, T_J=150^\circ\text{C}$	Fig. 20
T_J, T_{STG}	Operating Junction and Storage Temperature	-55 to +150	$^\circ\text{C}$		
T_L	Solder Temperature, 1.6mm from case for 10s	260	$^\circ\text{C}$		
M_d	Mounting Torque, (M3 or 6-32 screw)	1	Nm		
		8.8	lbf-in		



Electrical Characteristics ($T_c = 25^\circ\text{C}$ unless other

Symbol	Parameter	Min.	Typ.	Max.	Unit	Test Conditions	Note
$V_{(BR)DSS}$	Drain-Source Breakdown Voltage	1700			V	$V_{GS} = 0\text{ V}, I_D = 100\text{ }\mu\text{A}$	
$V_{GS(th)}$	Gate Threshold Voltage	2.0	2.8	4.3	V	$V_{DS} = V_{GS}, I_D = 0.5\text{ mA}$	Fig. 11
			2.4		V	$V_{DS} = V_{GS}, I_D = 0.5\text{ mA}, T_J = 150^\circ\text{C}$	
I_{DSS}	Zero Gate Voltage Drain Current		0.01	10	μA	$V_{DS} = 1.7\text{ kV}, V_{GS} = 0\text{ V}$	
I_{GSS}	Gate-Source Leakage Current			100	nA	$V_{GS} = 18\text{ V}, V_{DS} = 0\text{ V}$	
$R_{DS(on)}$	Drain-Source On-State Resistance		0.80	1.4	Ω	$V_{GS} = 18\text{ V}, I_D = 2\text{ A}$	Fig. 4,5,6
			1.4			$V_{GS} = 18\text{ V}, I_D = 2\text{ A}, T_J = 150^\circ\text{C}$	
g_{fs}	Transconductance		1.04		S	$V_{DS} = 18\text{ V}, I_{DS} = 2\text{ A}$	Fig. 7
			1.09			$V_{DS} = 18\text{ V}, I_{DS} = 2\text{ A}, T_J = 150^\circ\text{C}$	
C_{iss}	Input Capacitance		215		pF	$V_{GS} = 0\text{ V}$ $V_{DS} = 1000\text{ V}$ $f = 1\text{ MHz}$	Fig. 17,18
C_{oss}	Output Capacitance		19				
C_{rss}	Reverse Transfer Capacitance		2.2				
E_{oss}	C_{oss} Stored Energy		10.2		μJ	$V_{AC} = 25\text{ mV}$	Fig 16
E_{ON}	Turn-On Switching Energy		89		μJ	$V_{DS} = 1.2\text{ kV}, V_{GS} = -5/20\text{ V}$ $I_D = 2\text{ A}, R_{G(ext)} = 2.5\text{ }\Omega, L = 1478\text{ }\mu\text{H}, T_J = 150^\circ\text{C}$	Fig. 26
E_{OFF}	Turn Off Switching Energy		14				
$t_{d(on)}$	Turn-On Delay Time		5		ns	$V_{DD} = 1.2\text{ kV}, V_{GS} = -5/20\text{ V}$ $I_D = 2\text{ A}, R_{G(ext)} = 2.5\text{ }\Omega, R_L = 600\text{ }\Omega$ Timing relative to V_{DS} Per IEC60747-8-4 pg 83	Fig. 27
t_r	Rise Time		19				
$t_{d(off)}$	Turn-Off Delay Time		14				
t_f	Fall Time		63				
$R_{G(int)}$	Internal Gate Resistance		24.8		Ω	$f = 1\text{ MHz}, V_{AC} = 25\text{ mV}$	
Q_{gs}	Gate to Source Charge		4		nC	$V_{DS} = 1.2\text{ kV}, V_{GS} = -5/20\text{ V}$ $I_D = 2\text{ A}$ Per IEC60747-8-4 pg 21	Fig. 12
Q_{gd}	Gate to Drain Charge		12				
Q_g	Total Gate Charge		22				

Reverse Diode Characteristics

Symbol	Parameter	Typ.	Max.	Unit	Test Conditions	Note
V_{SD}	Diode Forward Voltage	3.8		V	$V_{GS} = -5\text{ V}, I_{SD} = 1\text{ A}, T_J = 25^\circ\text{C}$	Fig. 8, 9, 10
		3.3		V	$V_{GS} = -5\text{ V}, I_{SD} = 1\text{ A}, T_J = 150^\circ\text{C}$	
I_S	Continuous Diode Forward Current		4	A	$T_c = 25^\circ\text{C}$	Note 1
t_{rr}	Reverse Recovery Time	30		ns	$V_{GS} = -5\text{ V}, I_{SD} = 2\text{ A}, T_J = 150^\circ$ $C V_R = 1.2\text{ kV}$ $\text{diff/dt} = 1135\text{ A}/\mu\text{s}$	Note 1
Q_{rr}	Reverse Recovery Charge	31		nC		
I_{rrm}	Peak Reverse Recovery Current	3		A		

Note (1): When using SiC Body Diode the maximum recommended $V_{GS} = -5\text{V}$

Thermal Characteristics

Symbol	Parameter	Typ.	Max.	Unit	Test Conditions	Note
$R_{\theta JC}$	Thermal Resistance from Junction to Case	2.0	2.3	$^\circ\text{C}/\text{W}$		Fig. 21
$R_{\theta JA}$	Thermal Resistance from Junction to Ambient		50			



Typical Performance

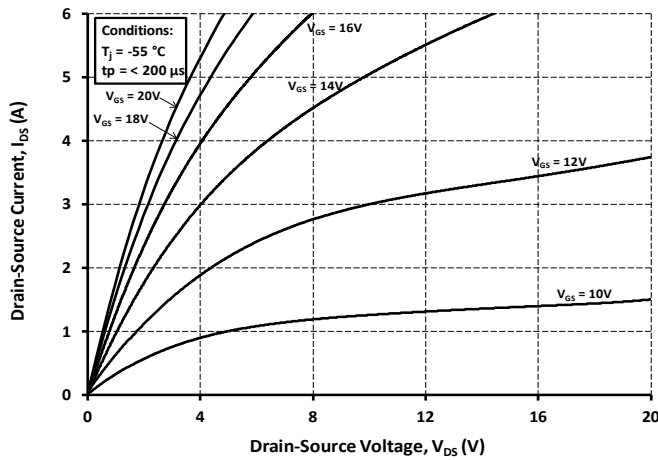


Figure 1. Output Characteristics $T_J = -55\text{ }^{\circ}\text{C}$

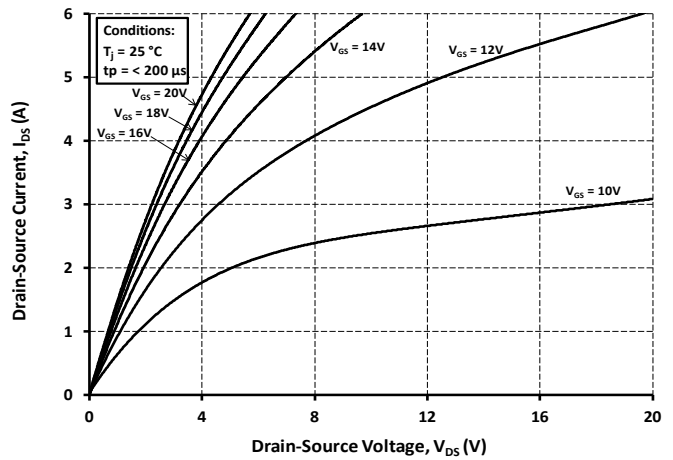


Figure 2. Output Characteristics $T_J = 25\text{ }^{\circ}\text{C}$

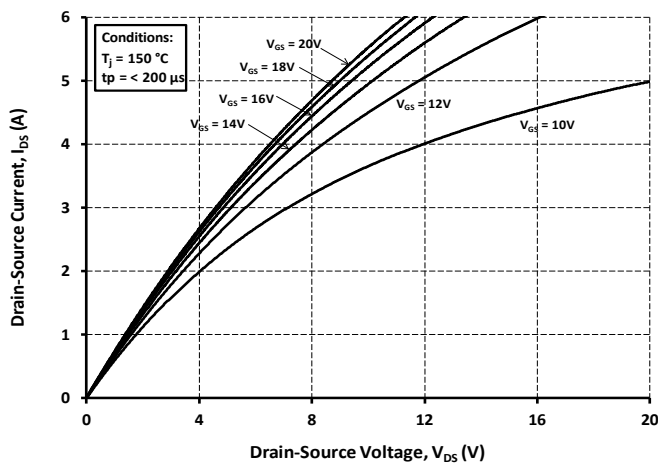


Figure 3. Output Characteristics $T_J = 150\text{ }^{\circ}\text{C}$

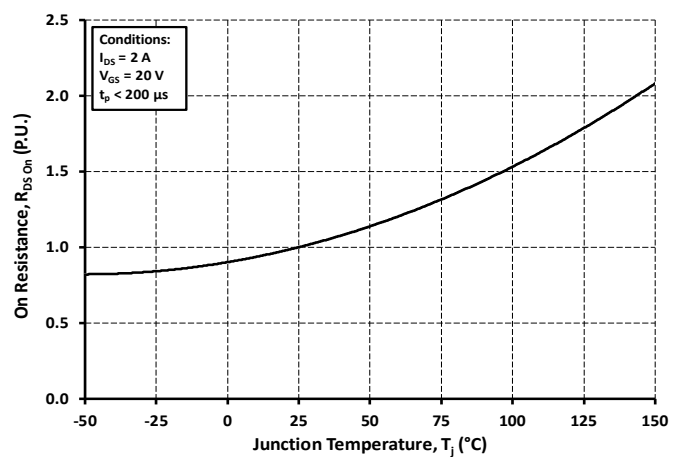


Figure 4. Normalized On-Resistance vs. Temperature

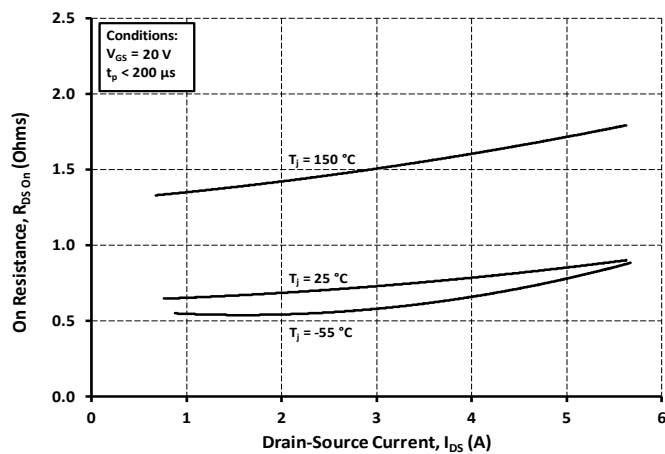


Figure 5. On-Resistance vs. Drain Current
For Various Temperatures

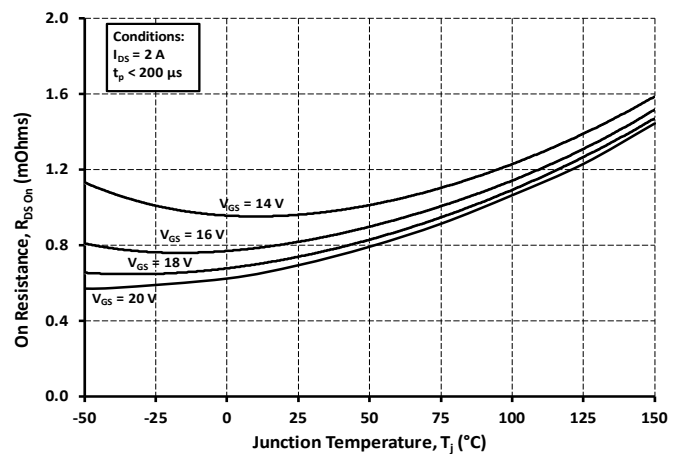


Figure 6. On-Resistance vs. Temperature
For Various Gate Voltage

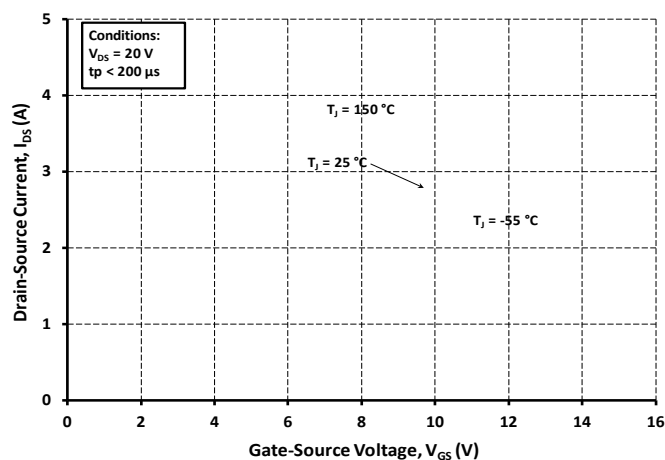


Figure 7. Transfer Characteristic for Various Junction Temperatures

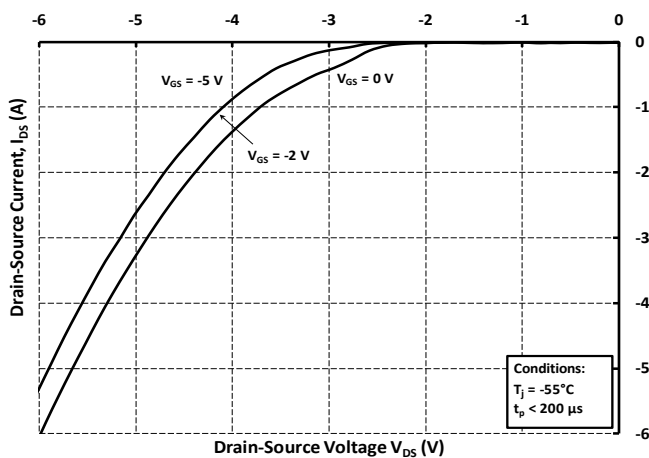


Figure 8. Body Diode Characteristic at $-55\text{ }^{\circ}\text{C}$

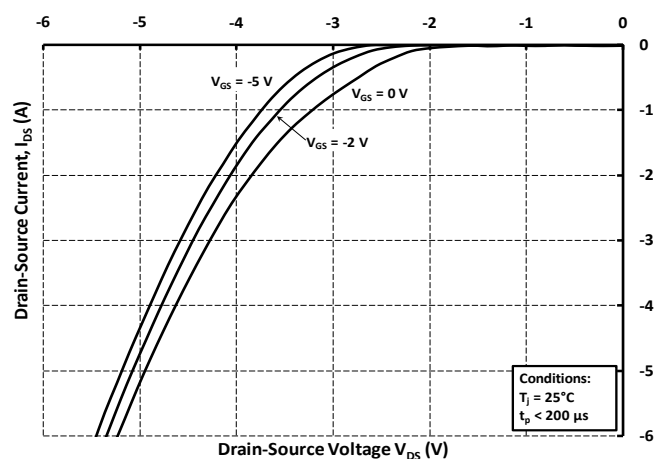


Figure 9. Body Diode Characteristic at $25\text{ }^{\circ}\text{C}$

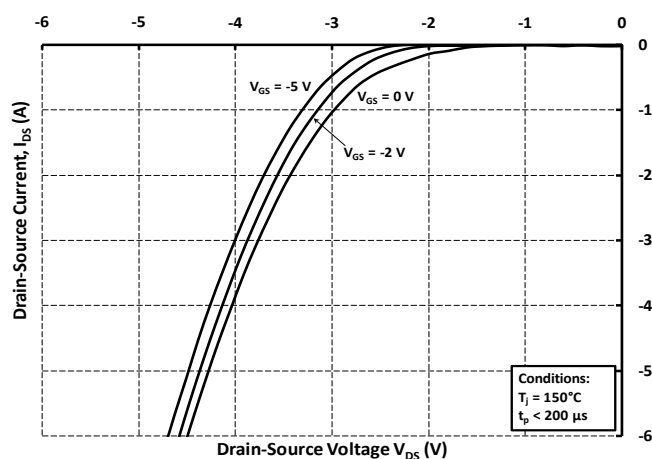


Figure 10. Body Diode Characteristic at $150\text{ }^{\circ}\text{C}$

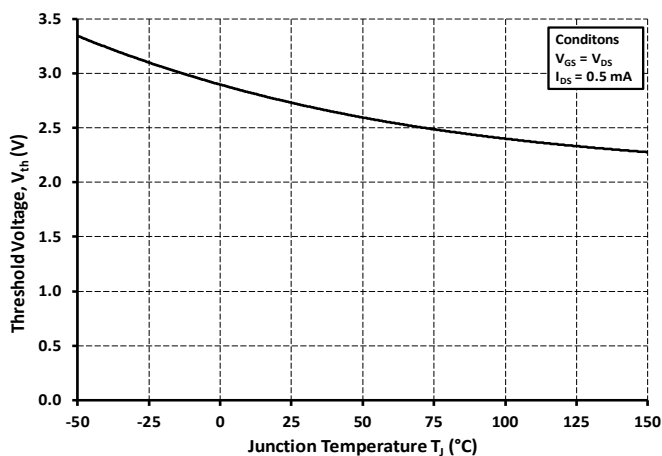


Figure 11. Threshold Voltage vs. Temperature

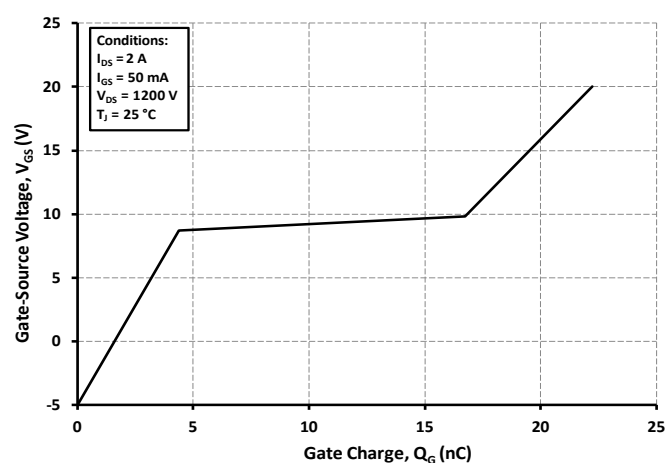


Figure 12. Gate Charge Characteristics

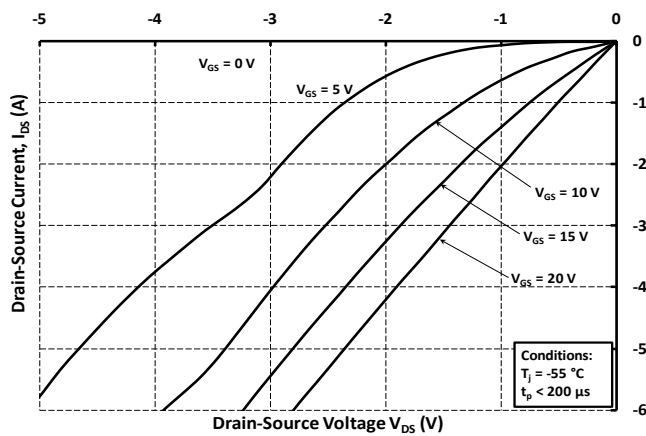


Figure 13. 3rd Quadrant Characteristic at -55 °C

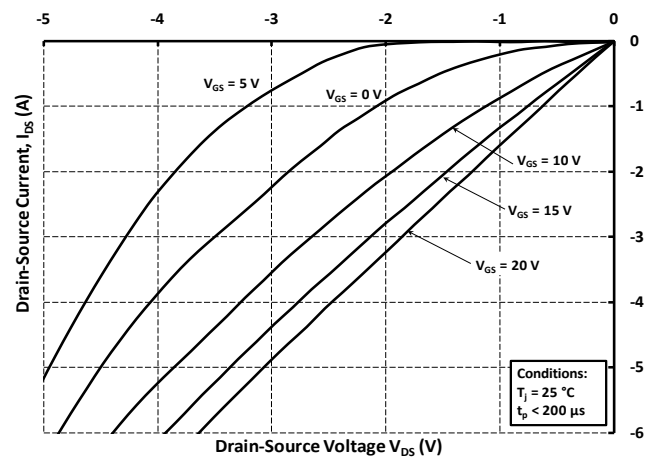


Figure 14. 3rd Quadrant Characteristic at 25 °C

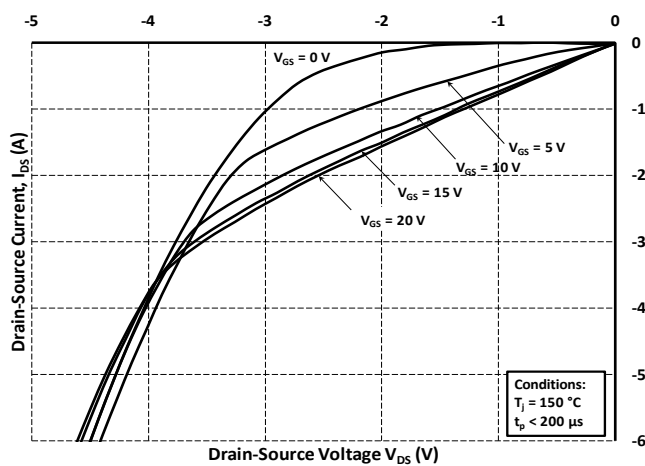


Figure 15. 3rd Quadrant Characteristic at 150 °C

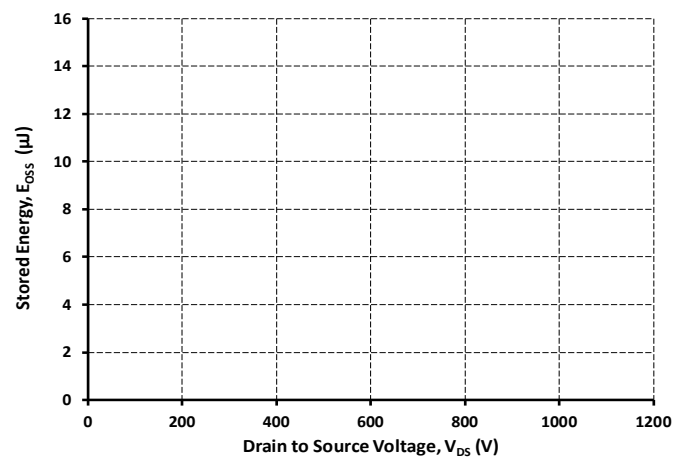


Figure 16 Output Capacitor Stored Energy

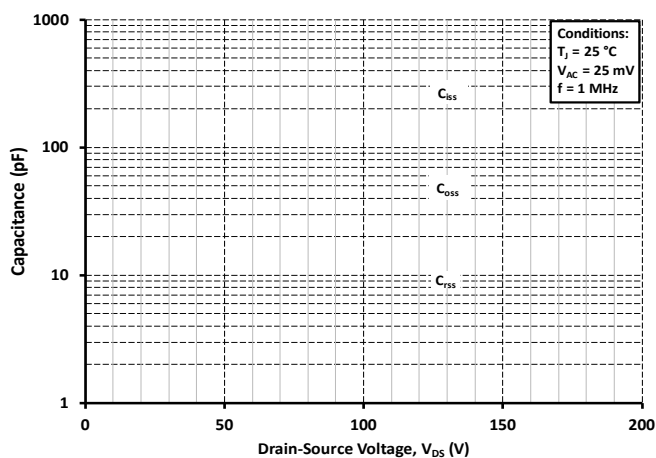


Figure 17. Capacitances vs. Drain-Source Voltage (0-200 V)

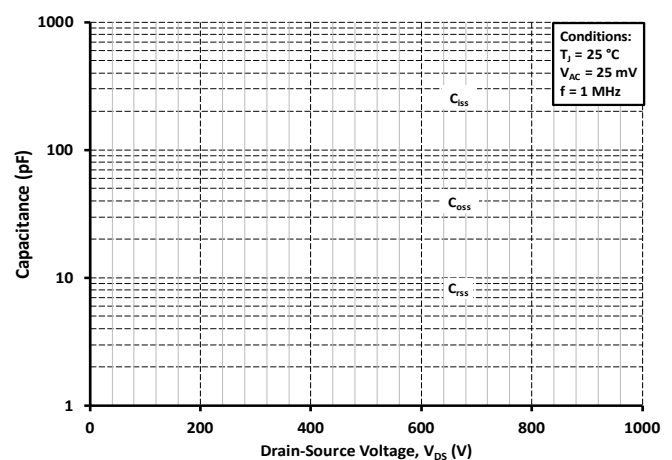


Figure 18. Capacitances vs. Drain-Source Voltage (0-1000 V)

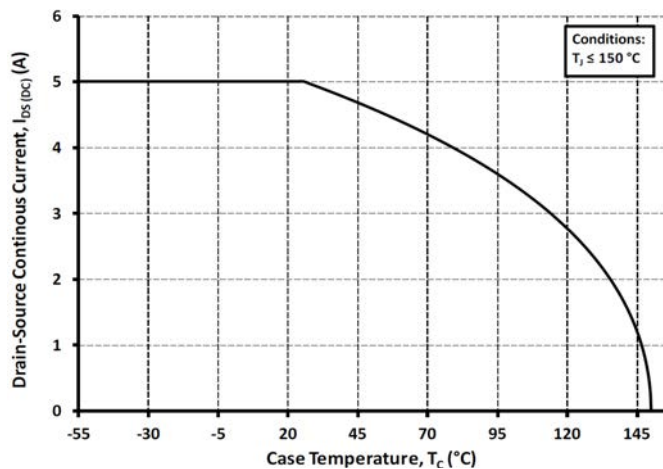


Figure 19. Continuous Drain Current Derating vs. Case Temperature

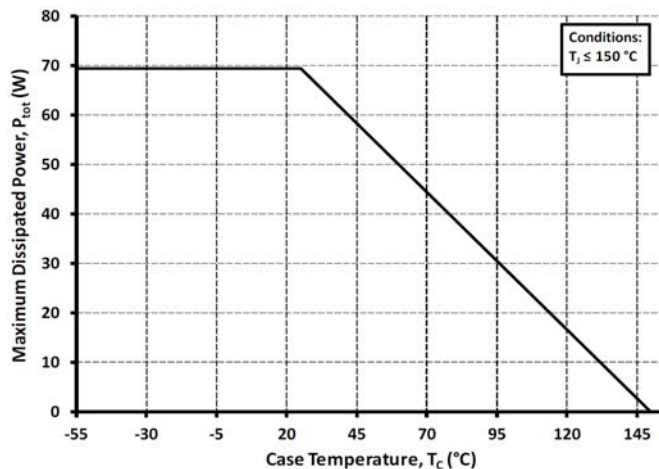


Figure 20. Maximum Power Dissipation Derating Vs Case Temperature

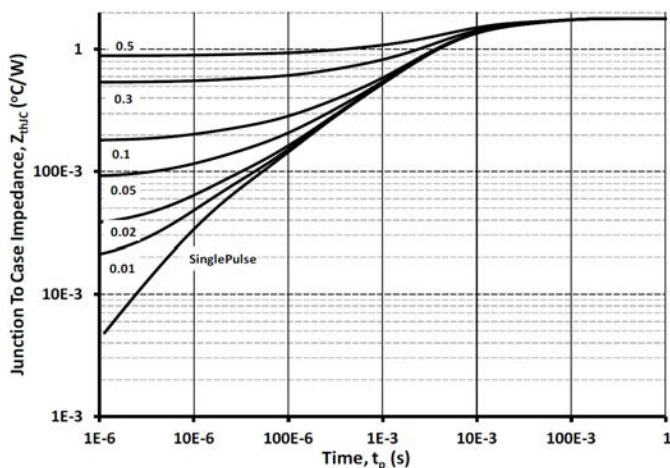


Figure 21. Transient Thermal Impedance (Junction - Case)

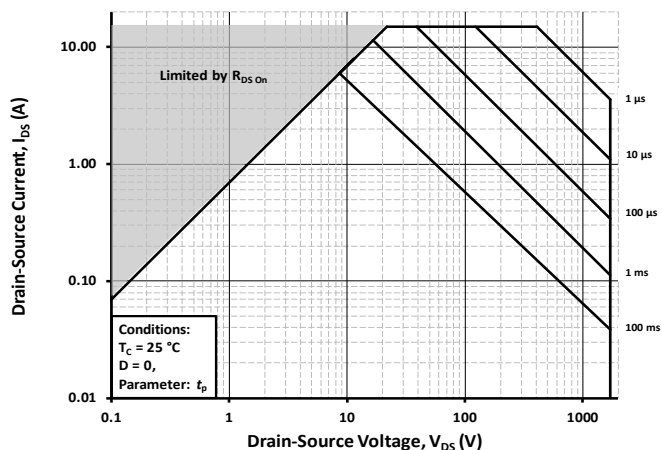


Figure 22. Safe Operating Area

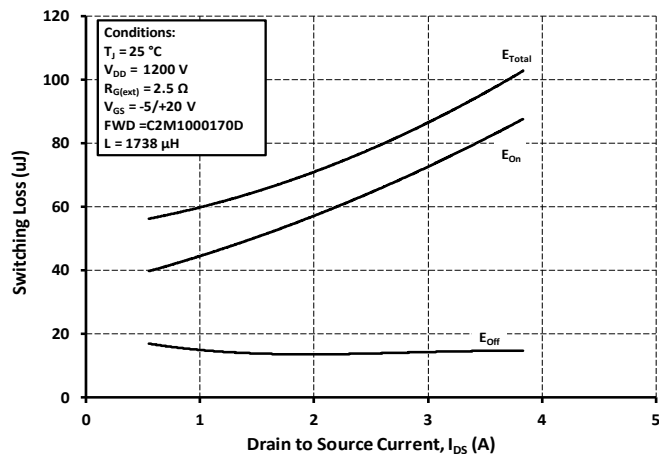


Figure 23. Clamped Inductive Switching Energy vs. Drain Current ($V_{DD} = 1200V$)

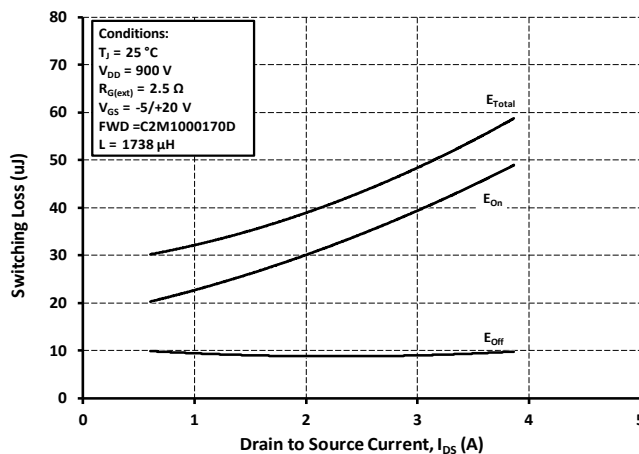


Figure 24. Clamped Inductive Switching Energy vs. Drain Current ($V_{DD} = 900V$)

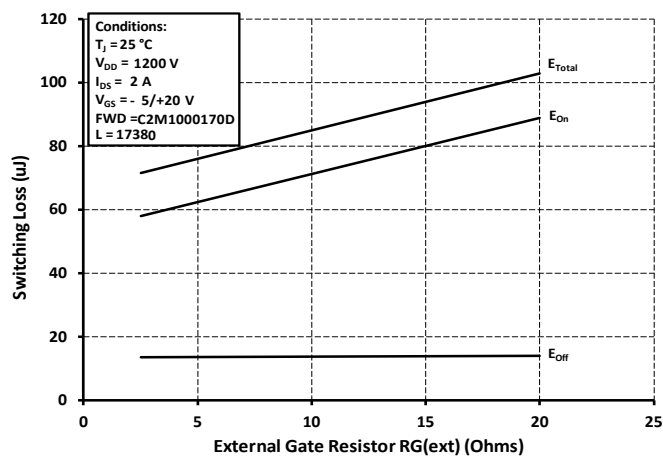


Figure 25. Clamped Inductive Switching Energy vs. $R_{G(\text{ext})}$

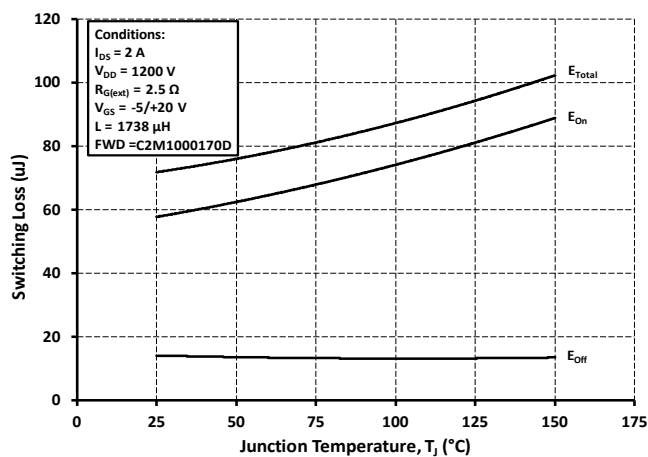


Figure 26. Clamped Inductive Switching Energy vs. Temperature

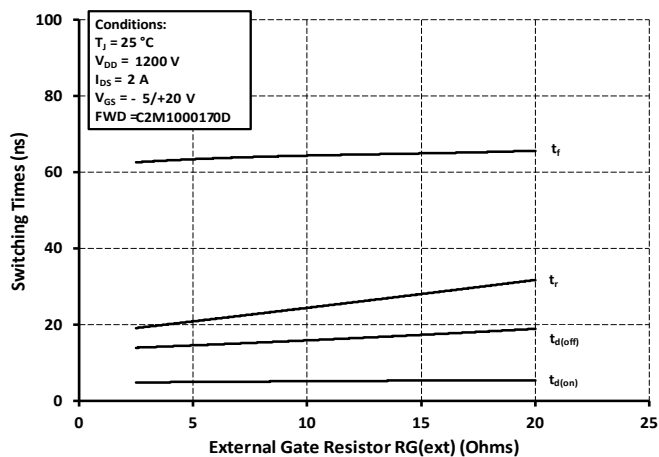


Figure 27. Switching Times vs. $R_{G(\text{ext})}$

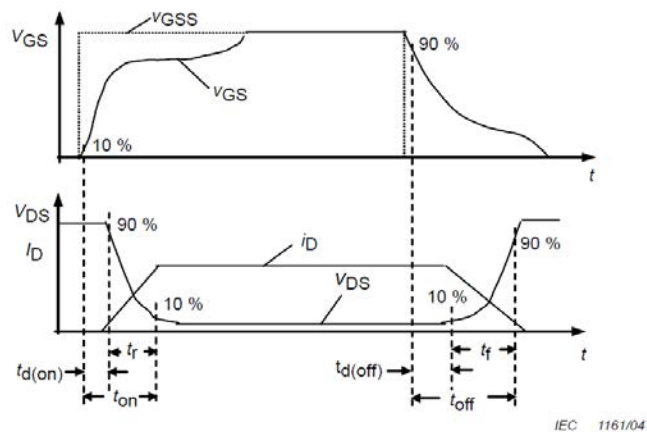


Figure 28. Switching Times Definition



Test Circuit Schematic

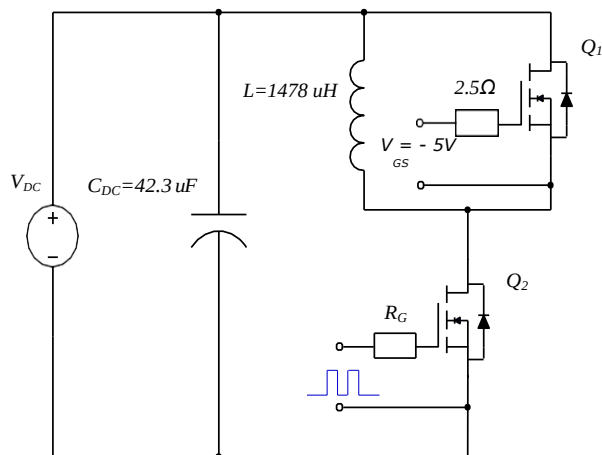


Figure 29. Clamped Inductive Switching
Waveform Test Circuit

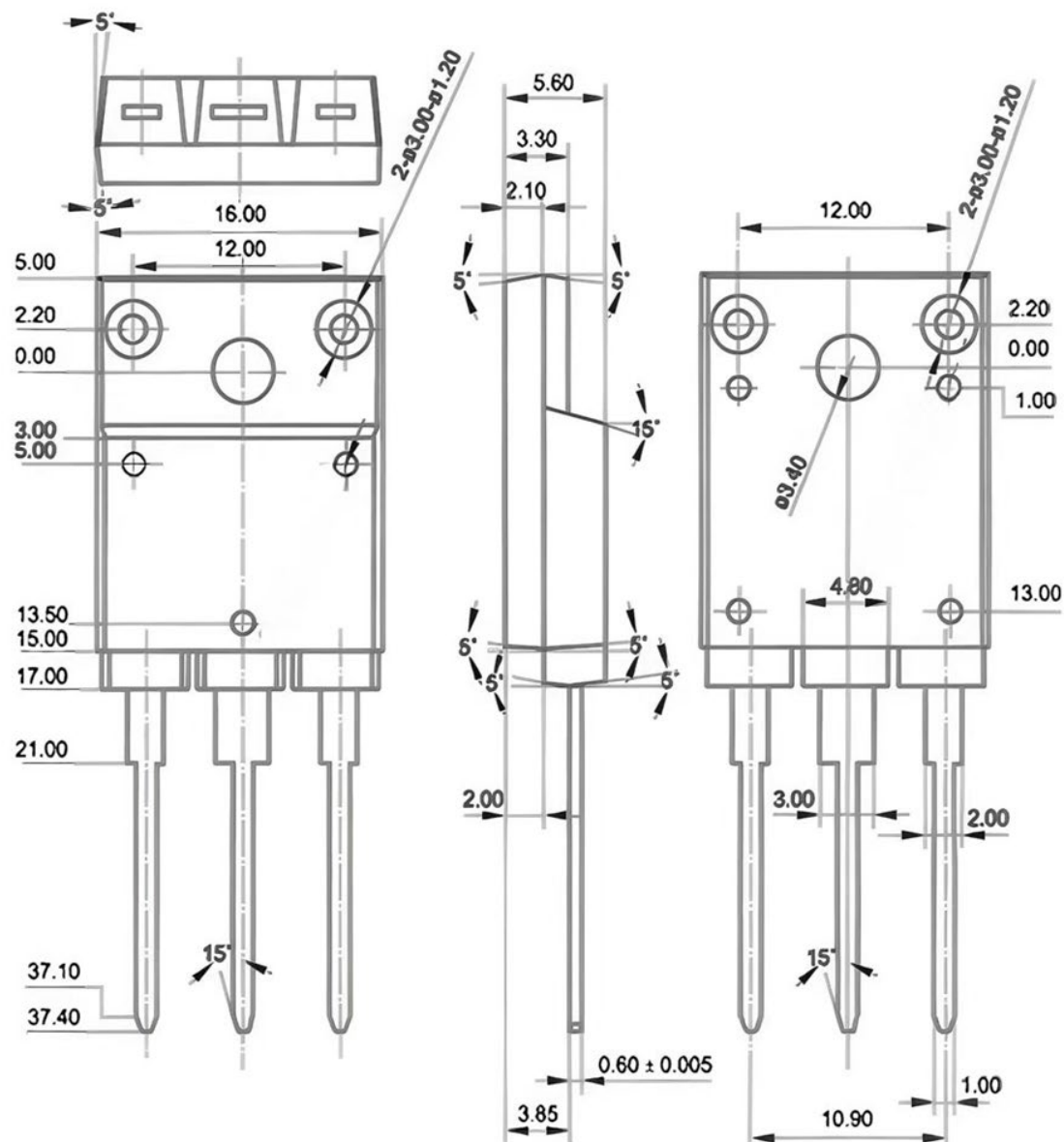
ESD Ratings

ESD Test	Total Devices Sampled	Resulting Classification
ESD-HBM	All Devices Passed 4000V	3A (>4000V)
ESD-CDM	All Devices Passed 1000V	IV (>1000V)



SiC Power MOSFET N-Channel Enhancement Mode

Package TO-3PF





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